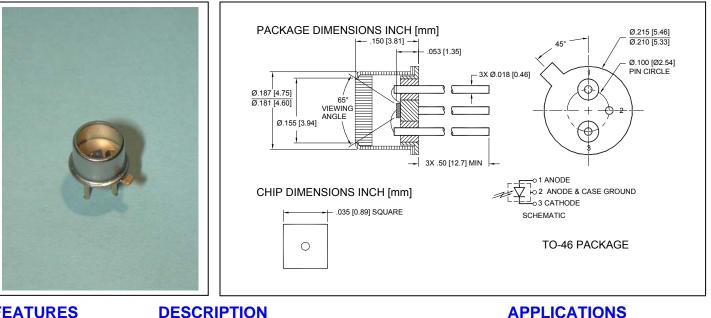
GaAIAs IR Photodiode **PDI-G103**





FEATURES

- Narrow response
- Daylight filtered ٠
- · Low cost

The PDI-G103 is a GaAlAs photodiode with a

spectral peak at 880nm and is immune to other ambient light. It is packaged in a TO-46 can package.

APPLICATIONS

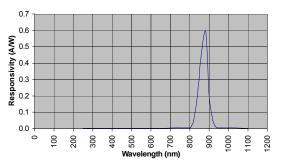
- · I.R. LED sensor
- I.R. links
- Industrial controls
- I.R. proximity sensor

ABSOLUTE MAXIMUM RATING (TA)= 23°C UNLESS OTHERWISE NOTED

SYMBOL	PARAMETER	MIN	MAX	UNITS	
V _{BR}	Reverse Voltage		100	V	
T _{STG}	Storage Temperature	-55	+100	°C	
To	Operating Temperature	-40	+100	°C	
Ts	Soldering Temperature*		+240	°C	

* 1/16 inch from case for 3 seconds max.

SPECTRAL RESPONSE



ELECTRO-OPTICAL CHARACTERISTICS RATING (TA)= 23°C UNLESS OTHERWISE NOTED

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	MIN	ТҮР	MAX	UNITS
I _{SC}	Short Circuit Current	H = 100 fc, 2850 K	5	6		μΑ
I _D	Dark Current	V _R = 5V		0.2	2	nA
R _{SH}	Shunt Resistance	V _R = 10 mV	1	3		GΩ
C」	Junction Capacitance	$V_R = 5V, f = 1 MHz$		90		pF
λ range	Spectral Application Range	Spot Scan	840		940	nm
R	Responsivity	λ = 880nm V, V _R = 0 V		0.60		A/W
V _{BR}	Breakdown Voltage	I = 10μA	20	30		V
NEP	Noise Equivalent Power	V _R = 10V @ λ = Peak		1X10 ⁻¹³		W/ $\sqrt{_{\rm Hz}}$
t _r	Response Time**	RL = 50 Ω,V _R = 5V		190		nS

**Response time of 10% to 90% is specified at 660nm wavelength light.

Information in this technical datasheet is believed to be correct and reliable. However, no responsibility is assumed for possible inaccuracies or omission. Specifications are subject to change without notice.